

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
100V	8.5mΩ @ V _{GS} = 10V	80A

Description

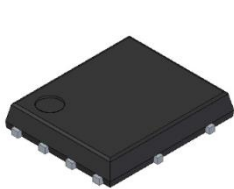
This new generation N-Channel Enhancement Mode MOSFET is designed to minimize R_{DS(ON)} yet maintain superior switching performance. This device is ideal for use in notebook battery power management and load switches.

Applications

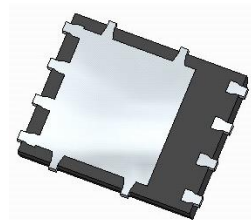
- Motor control
- DC-DC converters
- Power management

Site 1:

PowerDI5060-8

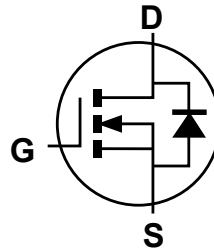


Top View

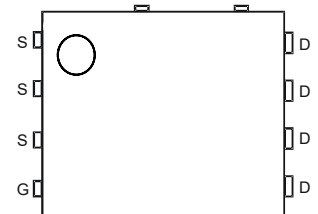


Bottom View

Pin 1



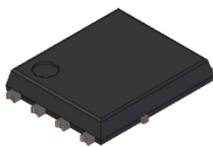
Internal Schematic



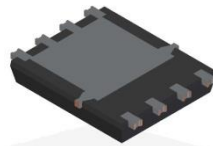
Top View
Pin Configuration

Site 2:

PowerDI5060-8/SWP (Type UX)

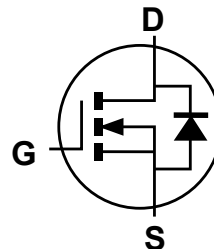


Top View

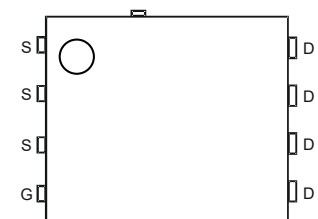


Bottom View

Pin 1



Internal Schematic



Top View
Pin Configuration

Notes:

1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

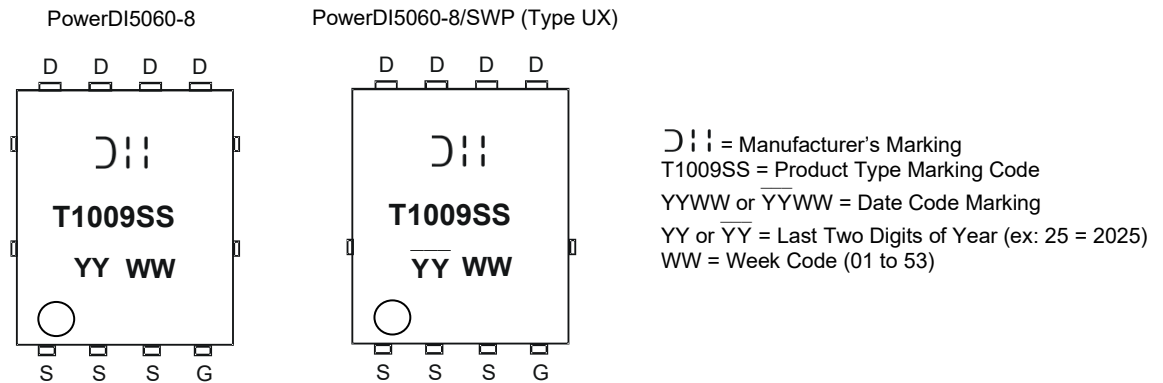
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Ordering Information (Note 4)

Orderable Part Number	Package	Packing	
		Qty.	Carrier
DMT10H009SPS-13	PowerDI5060-8	2,500	Tape & Reel
DMT10H009SPS-13	PowerDI5060-8/SWP (Type UX)	2,500	Tape & Reel

Note: 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	100	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current V _{GS} = 10V (Note 5)	Steady State	T _A = +25°C T _A = +70°C	I _D	14 11	A
Continuous Drain Current V _{GS} = 10V (Note 6)	Steady State	T _C = +25°C T _C = +70°C	I _D	80 64	A
Pulsed Drain Current (10μs Pulse, T _C = +25°C, Package Limited)			I _{DM}	320	A
Maximum Continuous Body Diode Forward Current			I _S	69	A
Pulsed Body Diode Current (10μs Pulse, T _C = +25°C, Package Limited)			I _{SM}	320	A
Avalanche Current (Note 7), L = 3mH			I _{AS}	11	A
Avalanche Energy (Note 7), L = 3mH			E _{AS}	181.5	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 8)	T _A = +25°C	P _D	1.3	W
Thermal Resistance, Junction to Ambient (Note 8)	Steady State	R _{θJA}	95	°C/W
Total Power Dissipation (Note 5)	T _A = +25°C	P _D	2.7	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	47	°C/W
Total Power Dissipation (Note 6)	T _C = +25°C	P _D	83	W
Thermal Resistance, Junction to Case (Note 6)		R _{θJC}	1.5	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
6. Thermal resistance from junction to soldering point (on the exposed drain pad).
7. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
8. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)						
Drain-Source Breakdown Voltage	BV _{DSS}	100	—	—	V	V _{GS} = 0, I _D = 1mA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	μA	V _{DS} = 80V, V _{GS} = 0
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0
ON CHARACTERISTICS (Note 9)						
Gate Threshold Voltage	V _{GS(TH)}	2	—	4	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	6.7	8.5	mΩ	V _{GS} = 10V, I _D = 20A
Diode Forward Voltage	V _{SD}	—	0.8	1.2	V	V _{GS} = 0, I _S = 13A
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C _{iss}	—	2085	—	pF	V _{DS} = 50V, V _{GS} = 0 f = 1MHz
Output Capacitance	C _{oss}	—	609	—		
Reverse Transfer Capacitance	C _{rss}	—	13	—		
Gate Resistance	R _g	—	1.7	—	Ω	V _{DS} = 0, V _{GS} = 0, f = 1MHz
Total Gate Charge (V _{GS} = 6V)	Q _g	—	19	—	nC	V _{DD} = 50V, I _D = 13A
Total Gate Charge (V _{GS} = 10V)	Q _g	—	30	—		
Gate-Source Charge	Q _{gs}	—	9.5	—		
Gate-Drain Charge	Q _{gd}	—	7.3	—		
Turn-On Delay Time	t _{D(ON)}	—	9.7	—	ns	V _{DD} = 50V, V _{GS} = 10V I _D = 13A, R _g = 6Ω
Turn-On Rise Time	t _R	—	13.7	—		
Turn-Off Delay Time	t _{D(OFF)}	—	25.1	—		
Turn-Off Fall Time	t _F	—	17.3	—		
Reverse-Recovery Time	t _{RR}	—	45	—	ns	I _F = 13A, di/dt = 100A/μs
Reverse-Recovery Charge	Q _{RR}	—	68	—	nC	

Notes: 9. Short duration pulse test used to minimize self-heating effect.
10. Guaranteed by design. Not subject to product testing.

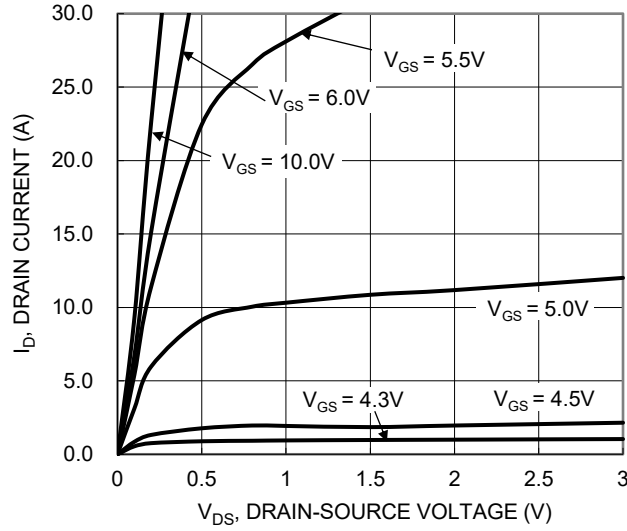


Figure 1. Typical Output Characteristic

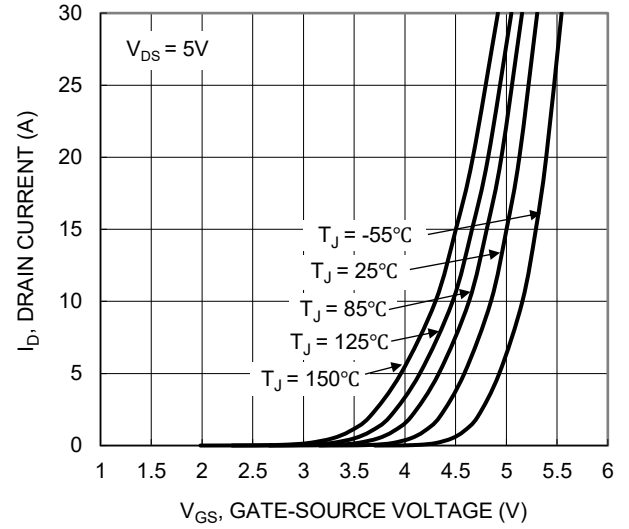


Figure 2. Typical Transfer Characteristic

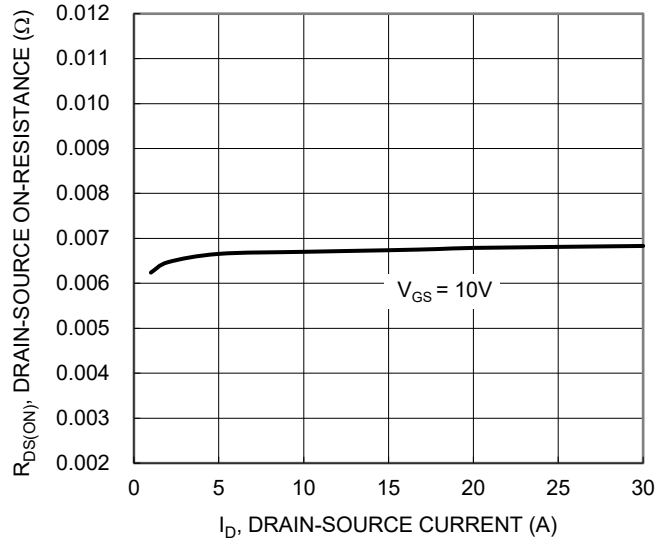


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

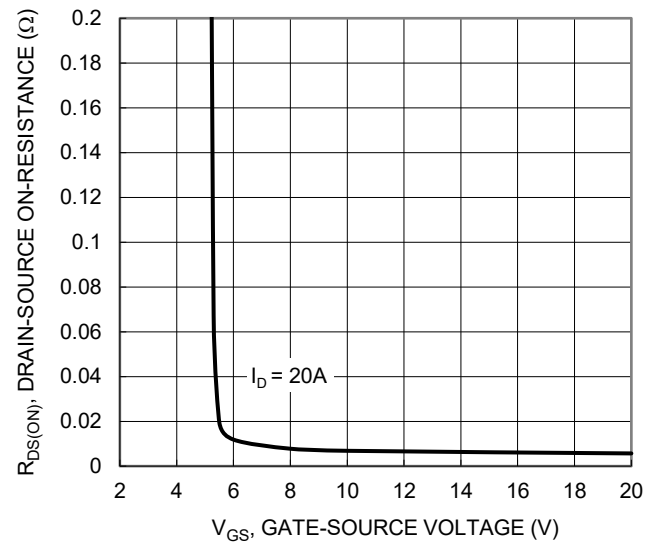


Figure 4. Typical Transfer Characteristic

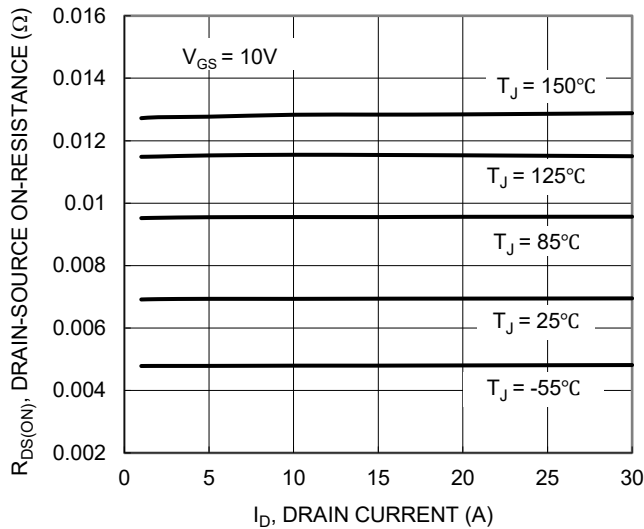


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

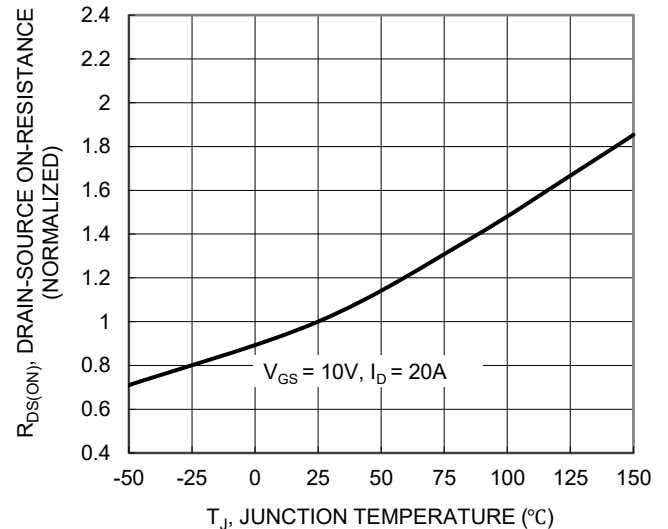


Figure 6. On-Resistance Variation with Temperature

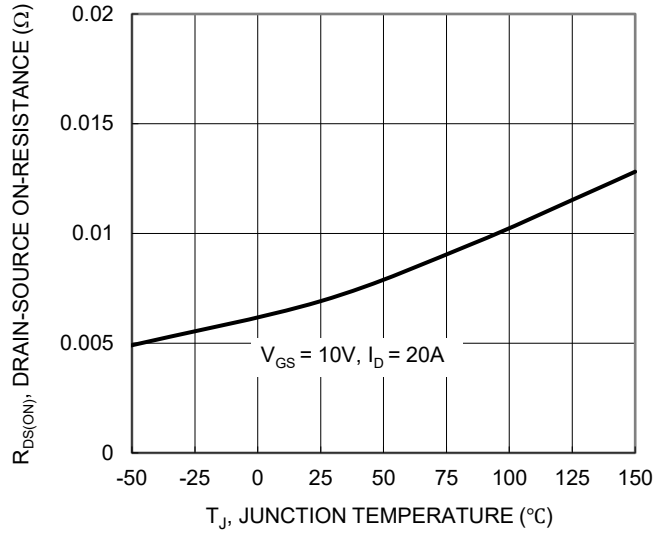


Figure 7. On-Resistance Variation with Temperature

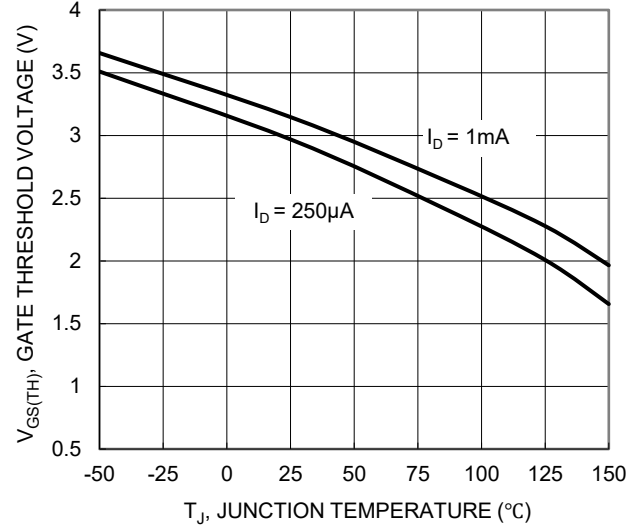


Figure 8. Gate Threshold Variation vs. Junction Temperature

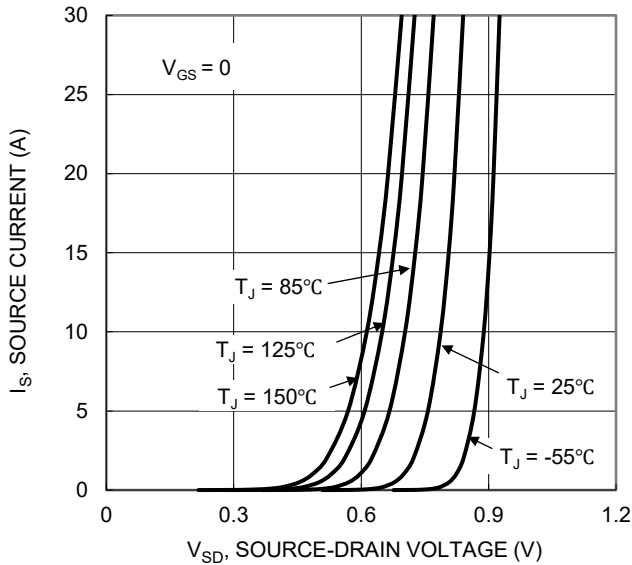


Figure 9. Diode Forward Voltage vs. Current

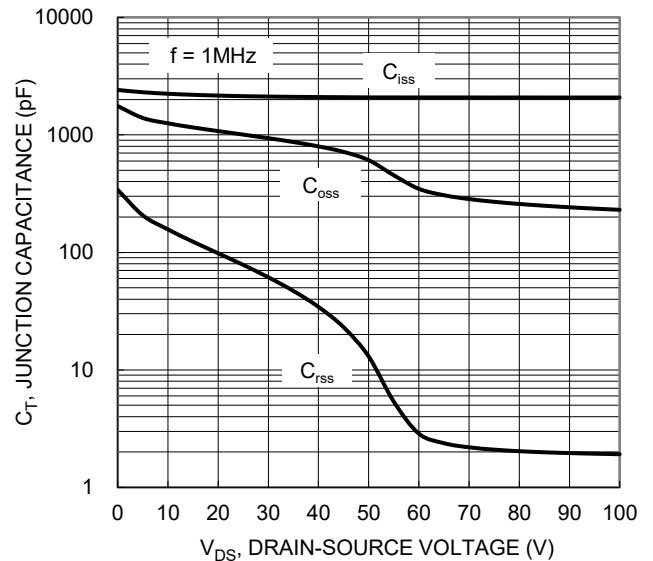


Figure 10. Typical Junction Capacitance

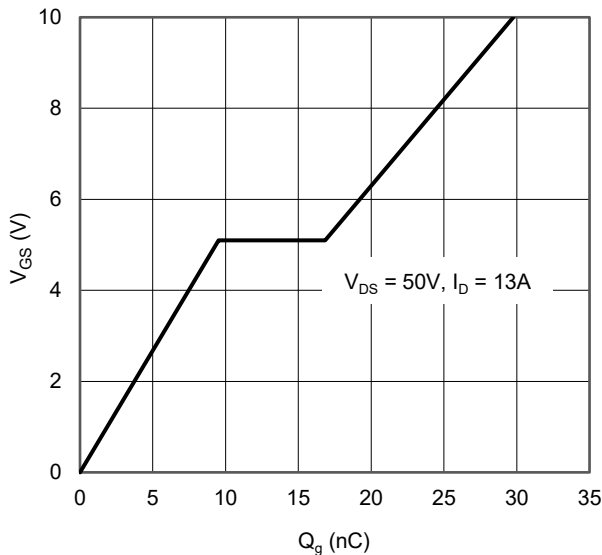


Figure 11. Gate Charge

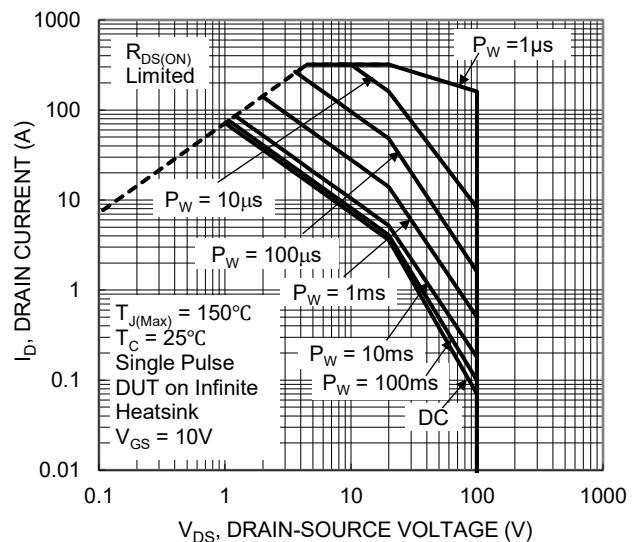


Figure 12. SOA, Safe Operation Area

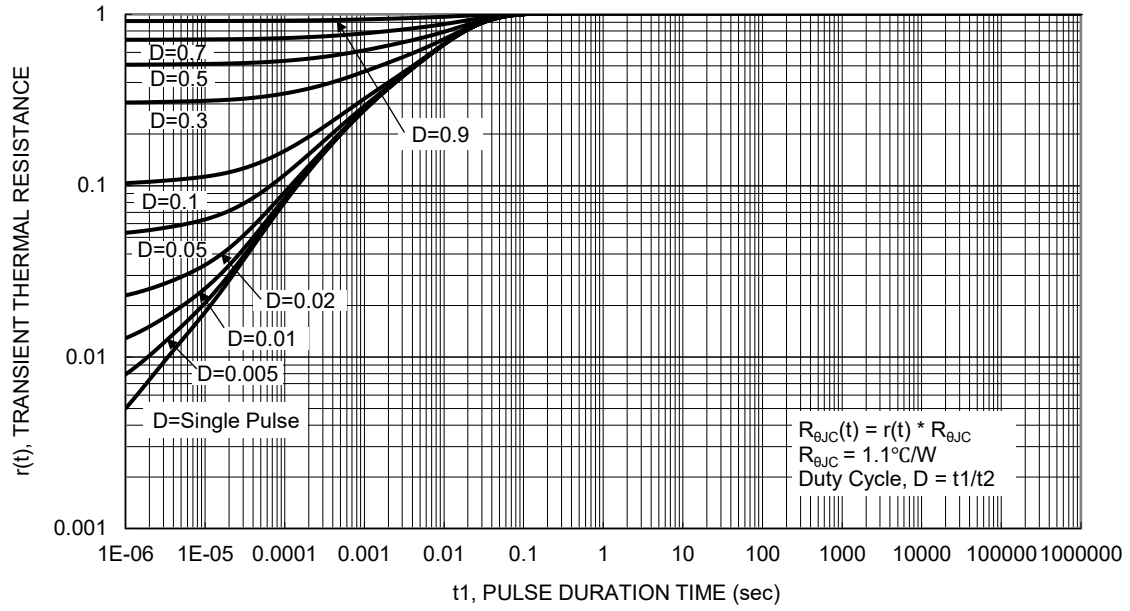


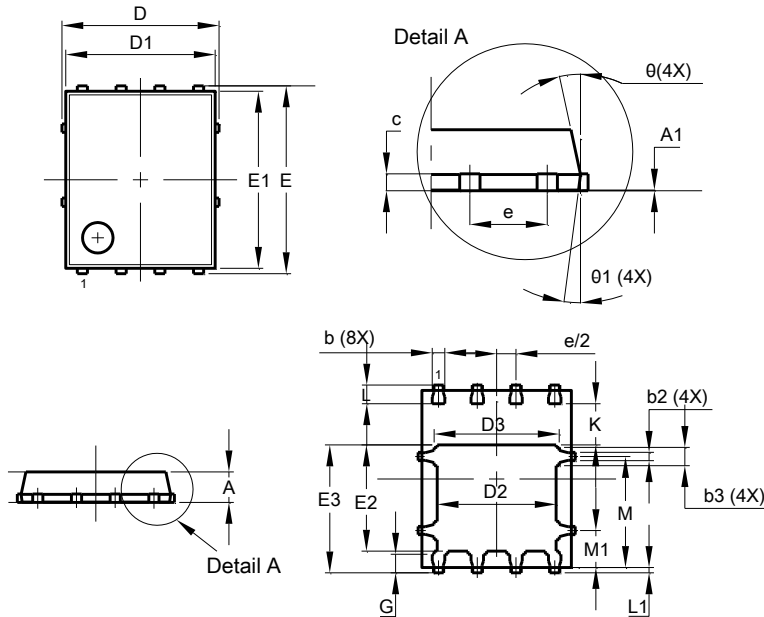
Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

Site 1:

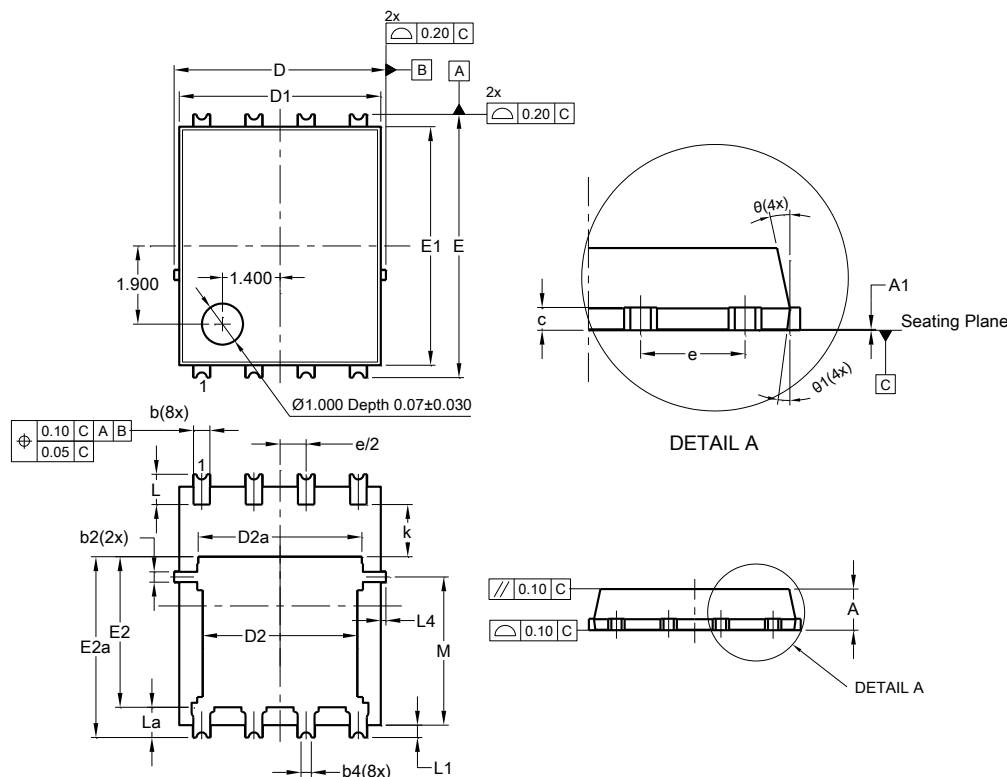
PowerDI5060-8



PowerDI5060-8			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0.00	0.05	—
b	0.33	0.51	0.41
b2	0.200	0.350	0.273
b3	0.40	0.80	0.60
c	0.230	0.330	0.277
D	5.15 BSC		
D1	4.70	5.10	4.90
D2	3.70	4.10	3.90
D3	3.90	4.30	4.10
E	6.15 BSC		
E1	5.60	6.00	5.80
E2	3.28	3.68	3.48
E3	3.99	4.39	4.19
e	1.27 BSC		
G	0.51	0.71	0.61
K	0.51	—	—
L	0.51	0.71	0.61
L1	0.100	0.200	0.175
M	3.235	4.035	3.635
M1	1.00	1.40	1.21
θ	10°	12°	11°
θ1	6°	8°	7°
All Dimensions in mm			

Site 2:

PowerDI5060-8/SWP (Type UX)



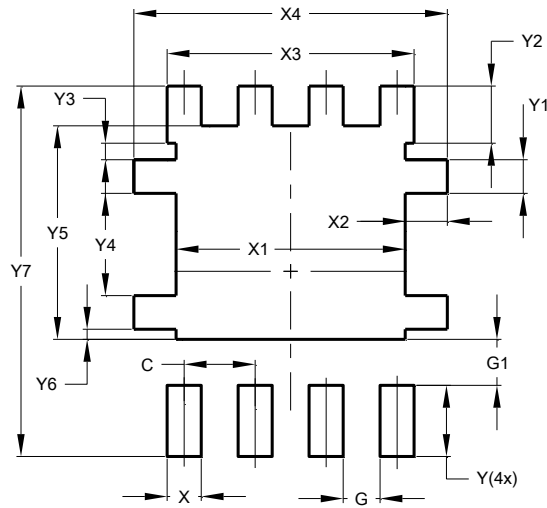
PowerDI5060-8/SWP (Type UX)			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0	0.05	—
b	0.30	0.50	0.41
b2	0.20	0.35	0.25
b4	0.25REF		
c	0.230	0.330	0.277
D	5.15 BSC		
D1	4.70	5.10	4.90
D2	3.56	3.96	3.76
D2a	3.78	4.18	3.98
E	6.40 BSC		
E1	5.60	6.00	5.80
E2	3.46	3.86	3.66
E2a	4.195	4.595	4.395
e	1.27BSC		
k	1.05	—	—
L	0.635	0.835	0.735
La	0.635	0.835	0.735
L1	0.200	0.400	0.300
L4	0.025	0.225	0.125
M	3.205	4.005	3.605
θ	10°	12°	11°
θ1	6°	8°	7°
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

Site 1:

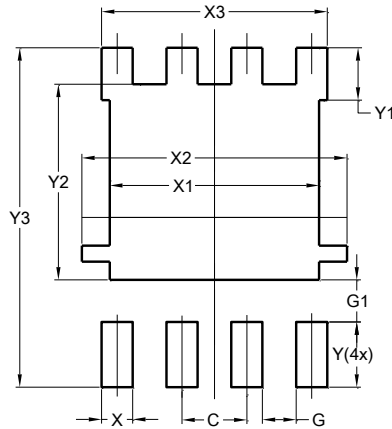
PowerDI5060-8



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	0.755
X3	4.420
X4	5.610
Y	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610

Site 2:

PowerDI5060-8/SWP (Type UX)



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	5.190
X3	4.420
Y	1.270
Y1	1.020
Y2	3.810
Y3	6.610

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